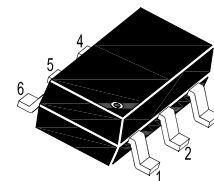
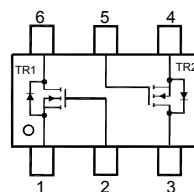




# THE DATASHEET OF 2N7002DW



## N-Channel Enhancement Mode Field Effect Transistor



1. Source 2. Gate 3. Drain  
4. Source 5. Gate 6. Drain

### ■ Simplified outline(SOT-363)

### ■ Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	60	V
Drain Gate Voltage ( $R_{GS} \leq 1 \text{ M}\Omega$ )	$V_{DGR}$	60	V
Gate Source Voltage	$V_{GSS}$	$\pm 20$	V
		$\pm 40$	
Drain Current	$I_D$	115	mA
		800	
Total Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	- 55 to + 150	$^\circ\text{C}$

### ■ Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Drain Source Breakdown Voltage at $I_D = 10 \mu\text{A}$	$BV_{DSS}$	60	-	V
Zero Gate Voltage Drain Current at $V_{DS} = 60 \text{ V}$	$I_{DSS}$	-	1	$\mu\text{A}$
Gate Source Leakage Current at $\pm V_{GS} = 20 \text{ V}$	$\pm I_{GSS}$	-	100	nA
Gate Source Threshold Voltage at $V_{DS} = V_{GS} = 10 \text{ V}$ , $I_D = 250 \mu\text{A}$	$V_{GS(th)}$	1	2.5	V
Static Drain Source On Resistance at $V_{GS} = 5 \text{ V}$ , $I_D = 50 \text{ mA}$ at $V_{GS} = 10 \text{ V}$ , $I_D = 500 \text{ mA}$	$R_{DS(ON)}$	-	7.5	$\Omega$
		-	7.5	
Drain Source On Voltage at $V_{GS} = 5 \text{ V}$ , $I_D = 50 \text{ mA}$ at $V_{GS} = 10 \text{ V}$ , $I_D = 500 \text{ mA}$	$V_{DS(ON)}$	-	1.5	V
		-	3.75	
Forward Transconductance at $V_{DS} = 10 \text{ V}$ , $I_D = 200 \text{ mA}$	$g_{FS}$	80	-	mS
Input Capacitance at $V_{DS} = 25 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{iss}$	-	50	pF
Output Capacitance at $V_{DS} = 25 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{oss}$	-	25	pF
Reverse Transfer Capacitance at $V_{DS} = 25 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{rss}$	-	5	pF
Turn On Time at $V_{DD} = 30\text{V}$ , $R_L = 150\Omega$ , $I_D = 0.2\text{A}$ , $V_{GS} = 10\text{V}$ , $R_{GEN} = 25\Omega$	$t_{on}$	-	20	ns
Turn Off Time at $V_{DD} = 30\text{V}$ , $R_L = 150\Omega$ , $I_D = 0.2\text{A}$ , $V_{GS} = 10\text{V}$ , $R_{GEN} = 25\Omega$	$t_{off}$	-	20	ns

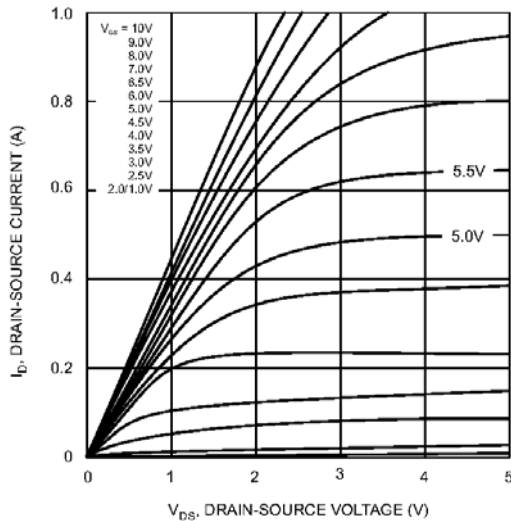


Fig. 1 On-Region Characteristics

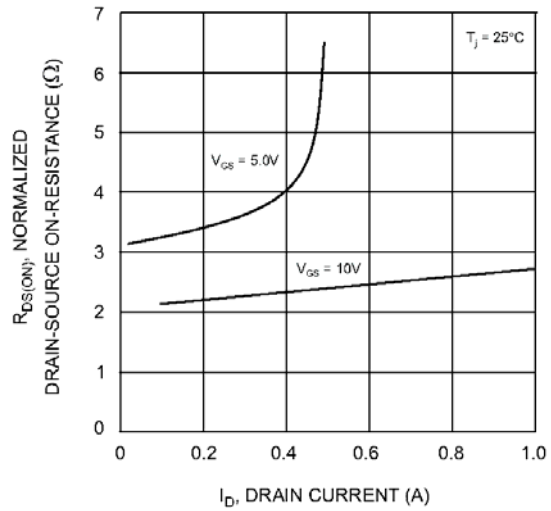


Fig. 2 On-Resistance vs Drain Current

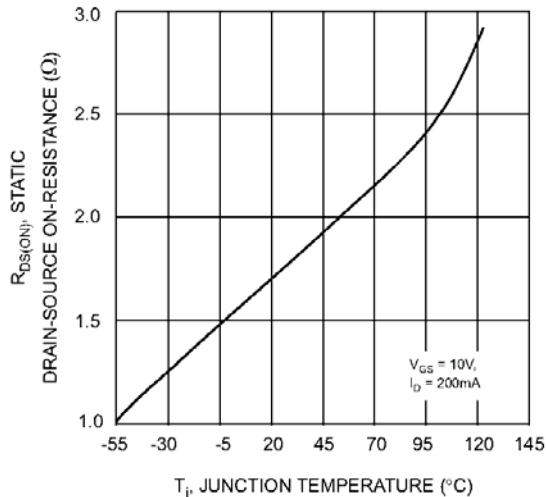


Fig. 3 On-Resistance vs Junction Temperature

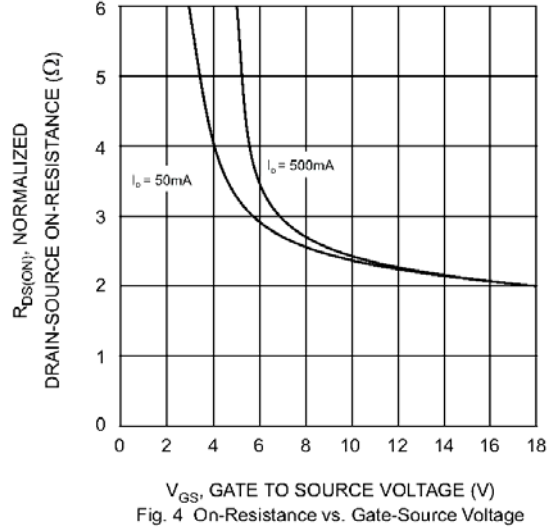


Fig. 4 On-Resistance vs. Gate-Source Voltage

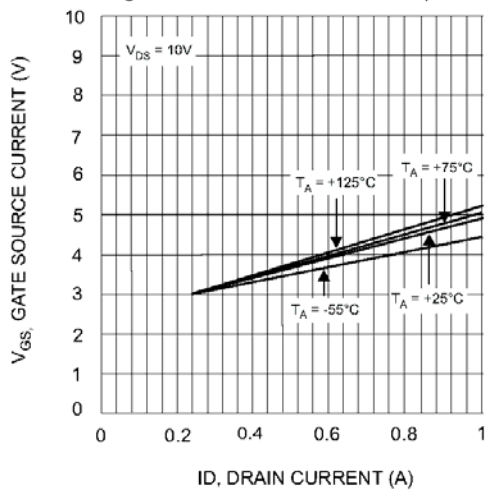
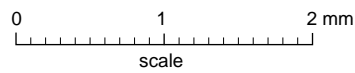
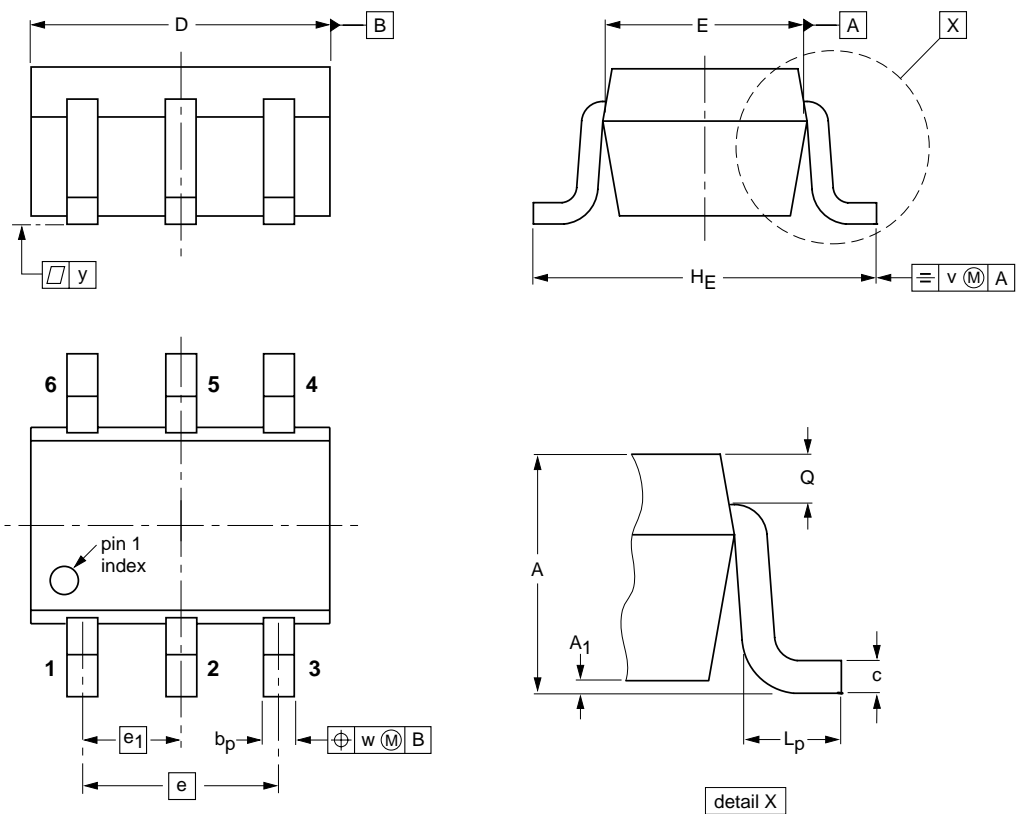


Fig. 5 Typical Transfer Characteristics

■ SOT-363



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

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